

Erik Janzen

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

624
papers

13,486
citations

58
h-index

88
g-index

632
ext. papers

14,625
ext. citations

2.2
avg, IF

6.03
L-index

#	Paper	IF	Citations
624	Wafer Scale On-Axis Homoepitaxial Growth of 4H-SiC(0001) for High-Power Devices: Influence of Different Gas Phase Chemistries and Growth Rate Limitations. <i>Crystal Growth and Design</i> , 2019 , 19, 3288-3297	3.5	4
623	Growth Mechanism of SiC Chemical Vapor Deposition: Adsorption and Surface Reactions of Active Si Species. <i>Journal of Physical Chemistry C</i> , 2018 , 122, 648-661	3.8	11
622	Defects in silicon carbide grown by fluorinated chemical vapor deposition chemistry. <i>Physica B: Condensed Matter</i> , 2018 , 535, 44-49	2.8	1
621	A GaN/SiC hybrid material for high-frequency and power electronics. <i>Applied Physics Letters</i> , 2018 , 113, 041605	3.4	32
620	Scalable Quantum Photonics with Single Color Centers in Silicon Carbide. <i>Nano Letters</i> , 2017 , 17, 1782-1786	8.5	85
619	Silicon Chemistry in Fluorinated Chemical Vapor Deposition of Silicon Carbide. <i>Journal of Physical Chemistry C</i> , 2017 , 121, 2711-2720	3.8	10
618	Incorporation of dopants in epitaxial SiC layers grown with fluorinated CVD chemistry. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2017 , 35, 031201	1.3	
617	Influence of n-Type Doping Levels on Carrier Lifetime in 4H-SiC Epitaxial Layers. <i>Materials Science Forum</i> , 2017 , 897, 238-241	0.4	1
616	Resonant optical spectroscopy and coherent control of Cr ⁴⁺ spin ensembles in SiC and GaN. <i>Physical Review B</i> , 2017 , 95,	3.3	42
615	Ab Initio Study of Growth Mechanism of 4H-SiC: Adsorption and Surface Reaction of C ₂ H ₂ , C ₂ H ₄ , CH ₄ , and CH ₃ . <i>Journal of Physical Chemistry C</i> , 2017 , 121, 1249-1256	3.8	13
614	Isolated Spin Qubits in SiC with a High-Fidelity Infrared Spin-to-Photon Interface. <i>Physical Review X</i> , 2017 , 7,	9.1	78
613	Matching precursor kinetics to afford a more robust CVD chemistry: a case study of the C chemistry for silicon carbide using SiF ₄ as Si precursor. <i>Journal of Materials Chemistry C</i> , 2017 , 5, 5818-5823	7.1	5
612	Scalable Quantum Photonics with Single Color Centers in Silicon Carbide 2017 ,		2
611	Chloride-based SiC growth on a-axis 4H-SiC substrates. <i>Physica B: Condensed Matter</i> , 2016 , 480, 23-25	2.8	1
610	ZrB ₂ thin films deposited on GaN(0001) by magnetron sputtering from a ZrB ₂ target. <i>Journal of Crystal Growth</i> , 2016 , 453, 71-76	1.6	5
609	Vector Magnetometry Using Silicon Vacancies in 4H-SiC Under Ambient Conditions. <i>Physical Review Applied</i> , 2016 , 6,	4.3	52
608	Deep level study of Mg-doped GaN using deep level transient spectroscopy and minority carrier transient spectroscopy. <i>Physical Review B</i> , 2016 , 94,	3.3	9

607	Performance Enhancement of Microwave GaN HEMTs Without an AlN-Exclusion Layer Using an Optimized AlGa _N /Ga _N Interface Growth Process. <i>IEEE Transactions on Electron Devices</i> , 2016 , 63, 333-338	2.9	12
606	A model for carbon incorporation from trimethyl gallium in chemical vapor deposition of gallium nitride. <i>Journal of Materials Chemistry C</i> , 2016 , 4, 863-871	7.1	16
605	Electronic properties of defects in high-fluence electron-irradiated bulk GaN. <i>Physica Status Solidi (B): Basic Research</i> , 2016 , 253, 521-526	1.3	3
604	Thermochemical Properties of Halides and Halohydrides of Silicon and Carbon. <i>ECS Journal of Solid State Science and Technology</i> , 2016 , 5, P27-P35	2	1
603	Development of an all-SiC neuronal interface device. <i>MRS Advances</i> , 2016 , 1, 3679-3684	0.7	5
602	Smooth 4H-SiC Epilayers Grown with High Growth Rates with Silane/Propane Chemistry Using 4 th Off-Cut Substrates. <i>Materials Science Forum</i> , 2016 , 858, 209-212	0.4	1
601	AlGa _N /Ga _N high electron mobility transistors with intentionally doped Ga _N buffer using propane as carbon precursor. <i>Japanese Journal of Applied Physics</i> , 2016 , 55, 05FK02	1.4	6
600	Electronic properties of Si-doped Al _x Ga _{1-x} N with aluminum mole fractions above 80%. <i>Journal of Applied Physics</i> , 2016 , 120, 145702	2.5	34
599	Deep levels in as-grown and electron-irradiated n-type GaN studied by deep level transient spectroscopy and minority carrier transient spectroscopy. <i>Journal of Applied Physics</i> , 2016 , 119, 095707	2.5	7
598	Long Charge Carrier Lifetime in As-Grown 4H-SiC Epilayer. <i>Materials Science Forum</i> , 2016 , 858, 125-128	0.4	
597	Impact of anharmonic effects on the phase stability, thermal transport, and electronic properties of AlN. <i>Physical Review B</i> , 2016 , 94,	3.3	16
596	Spin and photophysics of carbon-antisite vacancy defect in 4H silicon carbide: A potential quantum bit. <i>Physical Review B</i> , 2015 , 91,	3.3	41
595	Dispersive Effects in Microwave AlGa _N /AlN/GaN HEMTs With Carbon-Doped Buffer. <i>IEEE Transactions on Electron Devices</i> , 2015 , 62, 2162-2169	2.9	40
594	Graphene self-switching diodes as zero-bias microwave detectors. <i>Applied Physics Letters</i> , 2015 , 106, 093116	3.4	23
593	Precursors for carbon doping of GaN in chemical vapor deposition. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2015 , 33, 021208	1.3	29
592	Metalorganic chemical vapor deposition growth of high-mobility AlGa _N /AlN/GaN heterostructures on GaN templates and native GaN substrates. <i>Journal of Applied Physics</i> , 2015 , 117, 085301	2.5	9
591	Stoichiometric, epitaxial ZrB ₂ thin films with low oxygen-content deposited by magnetron sputtering from a compound target: Effects of deposition temperature and sputtering power. <i>Journal of Crystal Growth</i> , 2015 , 430, 55-62	1.6	23
590	Correlation between switching to n-type conductivity and structural defects in highly Mg-doped InN. <i>Applied Physics Letters</i> , 2015 , 106, 232102	3.4	7

589	On the behavior of silicon donor in conductive Al _x Ga _{1-x} N (0.63 ≤ x ≤ 1). <i>Physica Status Solidi (B): Basic Research</i> , 2015 , 252, 1306-1310	1.3	8
588	Low thermal resistance of a GaN-on-SiC transistor structure with improved structural properties at the interface. <i>Journal of Crystal Growth</i> , 2015 , 428, 54-58	1.6	18
587	The Role of Chlorine during High Growth Rate Epitaxy. <i>Materials Science Forum</i> , 2015 , 821-823, 141-144	0.4	5
586	Isolated electron spins in silicon carbide with millisecond coherence times. <i>Nature Materials</i> , 2015 , 14, 160-3	27	278
585	Coherent control of single spins in silicon carbide at room temperature. <i>Nature Materials</i> , 2015 , 14, 164-87	8	347
584	Quasi-free-standing monolayer and bilayer graphene growth on homoepitaxial on-axis 4H-SiC(0 0 0 1) layers. <i>Carbon</i> , 2015 , 82, 12-23	10.4	16
583	Optical properties and Zeeman spectroscopy of niobium in silicon carbide. <i>Physical Review B</i> , 2015 , 92,	3.3	5
582	Room-temperature mobility above 2200 cm ² /V ² s of two-dimensional electron gas in a sharp-interface AlGa _N /Ga _N heterostructure. <i>Applied Physics Letters</i> , 2015 , 106, 251601	3.4	33
581	In-grown stacking-faults in 4H-SiC epilayers grown on 2° off-cut substrates. <i>Physica Status Solidi (B): Basic Research</i> , 2015 , 252, 1319-1324	1.3	3
580	Shallow donor in natural MoS ₂ . <i>Physica Status Solidi - Rapid Research Letters</i> , 2015 , 9, 707-710	2.5	5
579	Theoretical model of dynamic spin polarization of nuclei coupled to paramagnetic point defects in diamond and silicon carbide. <i>Physical Review B</i> , 2015 , 92,	3.3	47
578	Properties of GaN layers grown on N-face free-standing GaN substrates. <i>Journal of Crystal Growth</i> , 2015 , 413, 81-85	1.6	2
577	Brominated Chemistry for Chemical Vapor Deposition of Electronic Grade SiC. <i>Chemistry of Materials</i> , 2015 , 27, 793-801	9.6	7
576	Assessment of H-intercalated graphene for microwave FETs through material characterization and electron transport studies. <i>Carbon</i> , 2015 , 81, 96-104	10.4	6
575	Characterization of InGa _N /Ga _N quantum well growth using monochromated valence electron energy loss spectroscopy. <i>Journal of Applied Physics</i> , 2014 , 115, 034302	2.5	3
574	Theoretical and electron paramagnetic resonance studies of hyperfine interaction in nitrogen doped 4H and 6H SiC. <i>Journal of Applied Physics</i> , 2014 , 115, 073705	2.5	16
573	On the use of methane as a carbon precursor in Chemical Vapor Deposition of silicon carbide. <i>Journal of Crystal Growth</i> , 2014 , 390, 24-29	1.6	12
572	Direct generation of linearly polarized photon emission with designated orientations from site-controlled InGa _N quantum dots. <i>Light: Science and Applications</i> , 2014 , 3, e139-e139	16.7	57

571	Carrier Mobility as a Function of Temperature in as-Grown and H-Intercalated Epitaxial Graphenes on 4H-SiC. <i>Materials Science Forum</i> , 2014 , 778-780, 1146-1149	0.4	1
570	Comparison of Carrier Lifetime Measurements and Mapping in 4H SiC Using Time Resolved Photoluminescence and EPCD. <i>Materials Science Forum</i> , 2014 , 778-780, 301-304	0.4	3
569	Oxidation Induced ON1, ON2a/b Defects in 4H-SiC Characterized by DLTS. <i>Materials Science Forum</i> , 2014 , 778-780, 281-284	0.4	2
568	Theoretical unification of hybrid-DFT and DFT + U methods for the treatment of localized orbitals. <i>Physical Review B</i> , 2014 , 90,	3.3	36
567	Finding the Optimum Chloride-Based Chemistry for Chemical Vapor Deposition of SiC. <i>ECS Journal of Solid State Science and Technology</i> , 2014 , 3, P320-P323	2	3
566	Carrier Lifetime Controlling Defects Z1/2 and RB1 in Standard and Chlorinated Chemistry Grown 4H-SiC. <i>Crystal Growth and Design</i> , 2014 , 14, 4104-4110	3.5	12
565	High thermal stability quasi-free-standing bilayer graphene formed on 4HSiC(0 0 0 1) via platinum intercalation. <i>Carbon</i> , 2014 , 79, 631-635	10.4	26
564	SiC Substrate effects on electron transport in the epitaxial graphene layer. <i>Electronic Materials Letters</i> , 2014 , 10, 387-391	2.9	4
563	Strain and morphology compliance during the intentional doping of high-Al-content AlGaN layers. <i>Applied Physics Letters</i> , 2014 , 105, 082106	3.4	11
562	Layer-number determination in graphene on SiC by reflectance mapping. <i>Carbon</i> , 2014 , 77, 492-500	10.4	46
561	Extraction and scattering analyses of 2D and bulk carriers in epitaxial graphene-on-SiC structure. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2014 , 63, 87-92	3	5
560	Hydrogen at zinc vacancy of ZnO: An EPR and ESEEM study 2014 ,		4
559	Quantitative comparison between Z1 $\bar{2}$ center and carbon vacancy in 4H-SiC. <i>Journal of Applied Physics</i> , 2014 , 115, 143705	2.5	33
558	Stable and metastable Si negative-U centers in AlGaN and AlN. <i>Applied Physics Letters</i> , 2014 , 105, 162106	3.4	41
557	Radiation-induced defects in GaN bulk grown by halide vapor phase epitaxy. <i>Applied Physics Letters</i> , 2014 , 105, 102103	3.4	17
556	Characterization of the nitrogen split interstitial defect in wurtzite aluminum nitride using density functional theory. <i>Journal of Applied Physics</i> , 2014 , 116, 113702	2.5	5
555	Magnetron sputtering of epitaxial ZrB ₂ thin films on 4H-SiC(0001) and Si(111). <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2014 , 211, 636-640	1.6	16
554	Fast Growth Rate Epitaxy on 4 $\bar{1}$ Off-Cut 4-Inch Diameter 4H-SiC Wafers. <i>Materials Science Forum</i> , 2014 , 778-780, 179-182	0.4	6

553	Resonant ionization of shallow donors in electric field. <i>Physica Scripta</i> , 2014 , 89, 085802	2.6	
552	High-Resolution Raman and Luminescence Spectroscopy of Isotope-Pure $^{28}\text{Si}^{12}\text{C}$, Natural and ^{13}C Enriched 4H-SiC. <i>Materials Science Forum</i> , 2014 , 778-780, 471-474	0.4	9
551	Homo-Epitaxial Growth on Low-Angle Off Cut 4H-SiC Substrate. <i>Materials Science Forum</i> , 2014 , 778-780, 131-134	0.4	1
550	Simulations of SiC CVD - Perspectives on the Need for Surface Reaction Model Improvements. <i>Materials Science Forum</i> , 2014 , 778-780, 218-221	0.4	0
549	Revisiting the Thermochemical Database of Si-C-H System Related to SiC CVD Modeling. <i>Materials Science Forum</i> , 2014 , 778-780, 175-178	0.4	1
548	Improved Epilayer Surface Morphology on 2° Off-Cut 4H-SiC Substrates. <i>Materials Science Forum</i> , 2014 , 778-780, 206-209	0.4	3
547	Theoretical Investigation of the Single Photon Emitter Carbon Antisite-Vacancy Pair in 4H-SiC. <i>Materials Science Forum</i> , 2014 , 778-780, 495-498	0.4	1
546	Identification of the Negative Carbon Vacancy at Quasi-Cubic Site in 4H-SiC by EPR and Theoretical Calculations. <i>Materials Science Forum</i> , 2014 , 778-780, 285-288	0.4	
545	Effect of Process Parameters on Dislocation Density in Thick 4H-SiC Epitaxial Layers Grown by Chloride-Based CVD on 4° Off-Axis Substrates. <i>Materials Science Forum</i> , 2014 , 778-780, 159-162	0.4	
544	Direct current magnetron sputtered ZrB ₂ thin films on 4H-SiC(0001) and Si(100). <i>Thin Solid Films</i> , 2014 , 550, 285-290	2.2	31
543	Impact of dielectric parameters on the reflectivity of 3C-BiC wafers with a rough surface morphology in the reststrahlen region. <i>Physica B: Condensed Matter</i> , 2014 , 439, 115-118	2.8	0
542	Electronic Defects in Electron-Irradiated Silicon Carbide and III-Nitrides 2014 , 417-451		
541	3C-SiC Heteroepitaxy on Hexagonal SiC Substrates. <i>Materials Science Forum</i> , 2013 , 740-742, 257-262	0.4	6
540	Structural Investigation of Heteroepitaxial 3C-SiC Grown on 4H-SiC Substrates. <i>Materials Science Forum</i> , 2013 , 740-742, 319-322	0.4	1
539	The charged exciton in an InGaN quantum dot on a GaN pyramid. <i>Applied Physics Letters</i> , 2013 , 103, 013102	1.9	5
538	Simulation of Gas-Phase Chemistry for Selected Carbon Precursors in Epitaxial Growth of SiC. <i>Materials Science Forum</i> , 2013 , 740-742, 213-216	0.4	2
537	A temperature dependent measurement of the carrier velocity vs. electric field characteristic for as-grown and H-intercalated epitaxial graphene on SiC. <i>Journal of Applied Physics</i> , 2013 , 113, 193708	2.5	19
536	Negative-U carbon vacancy in 4H-SiC: Assessment of charge correction schemes and identification of the negative carbon vacancy at the quasicubic site. <i>Physical Review B</i> , 2013 , 88,	3.3	39

535	Shortcomings of CVD modeling of SiC today. <i>Theoretical Chemistry Accounts</i> , 2013 , 132, 1	1.9	13
534	Adsorption and surface diffusion of silicon growth species in silicon carbide chemical vapour deposition processes studied by quantum-chemical computations. <i>Theoretical Chemistry Accounts</i> , 2013 , 132, 1	1.9	11
533	Process stability and morphology optimization of very thick 4H-SiC epitaxial layers grown by chloride-based CVD. <i>Journal of Crystal Growth</i> , 2013 , 380, 55-60	1.6	14
532	Thermal conductivity of isotopically enriched silicon carbide 2013 ,		4
531	Controlled growth of hexagonal GaN pyramids by hot-wall MOCVD. <i>Journal of Crystal Growth</i> , 2013 , 363, 287-293	1.6	12
530	Effective mass of electron in monolayer graphene: Electron-phonon interaction. <i>Journal of Applied Physics</i> , 2013 , 113, 043708	2.5	48
529	The influence of growth conditions on carrier lifetime in 4H-SiC epilayers. <i>Journal of Crystal Growth</i> , 2013 , 381, 43-50	1.6	10
528	Negative-U behavior of the Si donor in Al _{0.77} Ga _{0.23} N. <i>Applied Physics Letters</i> , 2013 , 103, 042101	3.4	8
527	Role of screening in the density functional applied to transition-metal defects in semiconductors. <i>Physical Review B</i> , 2013 , 87,	3.3	29
526	Reduction of structural defects in thick 4H-SiC epitaxial layers grown on 4° off-axis substrates. <i>Journal of Applied Physics</i> , 2013 , 113, 223502	2.5	23
525	Epitaxial growth of SiC with chlorinated precursors on different off-angle substrates. <i>Journal of Crystal Growth</i> , 2013 , 362, 170-173	1.6	11
524	Optical Properties of the Niobium Centre in 4H, 6H, and 15R SiC. <i>Materials Science Forum</i> , 2013 , 740-742, 405-408	0.4	1
523	Deterministic Single InGaN Quantum Dots grown on GaN Micro-Pyramid Arrays. <i>Advanced Materials Research</i> , 2013 , 646, 34-37	0.5	
522	Surface Evolution of 4H-SiC(0001) during In Situ Surface Preparation and its Influence on Graphene Properties. <i>Materials Science Forum</i> , 2013 , 740-742, 157-160	0.4	1
521	Morphology Optimization of Very Thick 4H-SiC Epitaxial Layers. <i>Materials Science Forum</i> , 2013 , 740-742, 251-254	0.4	
520	Photoluminescence of 8H-SiC. <i>Materials Science Forum</i> , 2013 , 740-742, 347-350	0.4	1
519	On-Axis Homoepitaxial Growth of 4H-SiC PiN Structure for High Power Applications. <i>Materials Science Forum</i> , 2013 , 740-742, 173-176	0.4	3
518	Electron Paramagnetic Resonance Studies of Nb in 6H-SiC. <i>Materials Science Forum</i> , 2013 , 740-742, 385-388		

517	Surface Preparation of 4° Off-Axis 4H-SiC Substrate for Epitaxial Growth. <i>Materials Science Forum</i> , 2013 , 740-742, 225-228	0.4	6
516	Influence of Growth Temperature on Carrier Lifetime in 4H-SiC Epilayers. <i>Materials Science Forum</i> , 2013 , 740-742, 637-640	0.4	4
515	Silicon and Oxygen in High-Al-Content AlGa _N : Incorporation Kinetics and Electron Paramagnetic Resonance Study. <i>Solid State Phenomena</i> , 2013 , 205-206, 441-445	0.4	2
514	Magnetic resonance identification of hydrogen at a zinc vacancy in ZnO. <i>Journal of Physics Condensed Matter</i> , 2013 , 25, 335804	1.8	12
513	The complex impact of silicon and oxygen on the n-type conductivity of high-Al-content AlGa _N . <i>Applied Physics Letters</i> , 2013 , 102, 132113	3.4	28
512	Investigation of deep levels in bulk GaN material grown by halide vapor phase epitaxy. <i>Journal of Applied Physics</i> , 2013 , 114, 153702	2.5	25
511	Electron effective mass in Al _{0.72} Ga _{0.28} N alloys determined by mid-infrared optical Hall effect. <i>Applied Physics Letters</i> , 2013 , 103, 212107	3.4	25
510	Impact of residual carbon on two-dimensional electron gas properties in Al _x Ga _{1-x} N/GaN heterostructure. <i>Applied Physics Letters</i> , 2013 , 102, 193506	3.4	68
509	Investigation on origin of Z1/2 center in SiC by deep level transient spectroscopy and electron paramagnetic resonance. <i>Applied Physics Letters</i> , 2013 , 102, 112106	3.4	44
508	Is the Registry Between Adjacent Graphene Layers Grown on C-Face SiC Different Compared to That on Si-Face SiC. <i>Crystals</i> , 2013 , 3, 1-13	2.3	9
507	The effect of grain size and phosphorous-doping of polycrystalline 3C-BiC on infrared reflectance spectra. <i>Journal of Nuclear Materials</i> , 2012 , 422, 103-108	3.3	3
506	Optical identification and electronic configuration of tungsten in 4H- and 6H-SiC. <i>Physica B: Condensed Matter</i> , 2012 , 407, 1462-1466	2.8	12
505	SiC epitaxy growth using chloride-based CVD. <i>Physica B: Condensed Matter</i> , 2012 , 407, 1467-1471	2.8	12
504	Optical characterization of individual quantum dots. <i>Physica B: Condensed Matter</i> , 2012 , 407, 1472-1475	2.8	2
503	The origin of a peak in the reststrahlen region of SiC. <i>Physica B: Condensed Matter</i> , 2012 , 407, 1525-1528	2.8	6
502	Negative-U system of carbon vacancy in 4H-SiC. <i>Physical Review Letters</i> , 2012 , 109, 187603	7.4	176
501	Polarized and diameter-dependent Raman scattering from individual aluminum nitride nanowires: The antenna and cavity effects. <i>Applied Physics Letters</i> , 2012 , 101, 121902	3.4	13
500	Temperature dependent effective mass in AlGa _N /GaN high electron mobility transistor structures. <i>Applied Physics Letters</i> , 2012 , 101, 192102	3.4	34

499	Observation of the generation of stacking faults and active degradation measurements on off-axis and on-axis 4H-SiC PIN diodes. <i>Applied Physics Letters</i> , 2012 , 101, 222111	3.4	16
498	Gas-Phase Modeling of Chlorine-Based Chemical Vapor Deposition of Silicon Carbide. <i>Crystal Growth and Design</i> , 2012 , 12, 1977-1984	3.5	15
497	Influence of Large-Aspect-Ratio Surface Roughness on Electrical Characteristics of AlGaN/AlN/GaN HFETs. <i>IEEE Transactions on Device and Materials Reliability</i> , 2012 , 12, 538-546	1.6	5
496	Chloride-based CVD growth of silicon carbide for electronic applications. <i>Chemical Reviews</i> , 2012 , 112, 2434-53	68.1	80
495	InGaN quantum dot formation mechanism on hexagonal GaN/InGaN/GaN pyramids. <i>Nanotechnology</i> , 2012 , 23, 305708	3.4	23
494	High-quality AlN layers grown by hot-wall MOCVD at reduced temperatures. <i>Journal of Crystal Growth</i> , 2012 , 338, 52-56	1.6	43
493	Effects of phosphorous-doping and high temperature annealing on CVD grown 3C-SiC. <i>Nuclear Engineering and Design</i> , 2012 , 251, 191-202	1.8	4
492	Morphology Control of Hot-Wall MOCVD Selective Area Grown Hexagonal GaN Pyramids. <i>Crystal Growth and Design</i> , 2012 , 12, 5491-5496	3.5	30
491	Capacitance transient study of a bistable deep level in eIrradiated n-type 4HSiC. <i>Journal Physics D: Applied Physics</i> , 2012 , 45, 455301	3	13
490	Carrot Defect Control in Chloride-Based CVD through Optimized Ramp up Conditions. <i>Materials Science Forum</i> , 2012 , 717-720, 109-112	0.4	6
489	Radial Variation of Measured Carrier Lifetimes in Epitaxial Layers Grown with Wafer Rotation. <i>Materials Science Forum</i> , 2012 , 717-720, 289-292	0.4	1
488	Investigation of Intrinsic Carbon-Related Defects in 4H-SiC by Selective-Excitation Photoluminescence Spectroscopy. <i>Materials Science Forum</i> , 2012 , 717-720, 259-262	0.4	1
487	Chloride-Based CVD of 4H-SiC at High Growth Rates on Substrates with Different Off-Angles. <i>Materials Science Forum</i> , 2012 , 717-720, 113-116	0.4	2
486	Control of Epitaxial Graphene Thickness on 4H-SiC(0001) and Buffer Layer Removal through Hydrogen Intercalation. <i>Materials Science Forum</i> , 2012 , 717-720, 605-608	0.4	8
485	CVD Heteroepitaxial Growth of 3C-SiC on 4H-SiC (0001) Substrates. <i>Materials Science Forum</i> , 2012 , 717-720, 189-192	0.4	2
484	Electronic Configuration of Tungsten in 4H-, 6H-, and 15R-SiC. <i>Materials Science Forum</i> , 2012 , 717-720, 211-216	0.4	
483	Identification of Niobium in 4H-SiC by EPR and Ab Initio Studies. <i>Materials Science Forum</i> , 2012 , 717-720, 217-220	0.4	3
482	CVD Growth of 3C-SiC on 4H-SiC Substrate. <i>Materials Science Forum</i> , 2012 , 711, 16-21	0.4	2

481	The Effect of Growth Conditions on Carrier Lifetime in N-Type 4H-SiC Epitaxial Layers. <i>Materials Science Forum</i> , 2012 , 717-720, 161-164	0.4	4
480	High-Resolution Time-Resolved Carrier Lifetime and Photoluminescence Mapping of 4H-SiC Epilayers. <i>Materials Science Forum</i> , 2012 , 717-720, 293-296	0.4	2
479	Electron paramagnetic resonance and theoretical studies of Nb in 4H- and 6H-SiC. <i>Journal of Applied Physics</i> , 2012 , 112, 083711	2.5	10
478	Electrical and Optical Properties of High-Purity Epilayers Grown by the Low-Temperature Chloro-Carbon Growth Method. <i>Materials Science Forum</i> , 2012 , 717-720, 129-132	0.4	1
477	Influence of Growth Mechanism on Carrier Lifetime in On-Axis Homoepitaxial Layers of 4H-SiC. <i>Materials Science Forum</i> , 2012 , 717-720, 157-160	0.4	1
476	Transition Metal Defects in Cubic and Hexagonal Polytypes of SiC: Site Selection, Magnetic and Optical Properties from Ab Initio Calculations. <i>Materials Science Forum</i> , 2012 , 717-720, 205-210	0.4	2
475	Growth and characterization of epitaxial ultra-thin NbN films on 3C-SiC/Si substrate for terahertz applications. <i>Superconductor Science and Technology</i> , 2011 , 24, 035016	3.1	20
474	Chloride-Based CVD at High Rates of 4H-SiC on On-Axis Si-Face Substrates. <i>Materials Science Forum</i> , 2011 , 679-680, 59-62	0.4	7
473	High Growth Rate with Reduced Surface Roughness during On-Axis Homoepitaxial Growth of 4H-SiC. <i>Materials Science Forum</i> , 2011 , 679-680, 115-118	0.4	5
472	Deep levels in tungsten doped n-type 3CβSiC. <i>Applied Physics Letters</i> , 2011 , 98, 152104	3.4	15
471	Deep levels in iron doped n- and p-type 4H-SiC. <i>Journal of Applied Physics</i> , 2011 , 110, 123701	2.5	17
470	Annealing behavior of the EB-centers and M-center in low-energy electron irradiated n-type 4H-SiC. <i>Journal of Applied Physics</i> , 2011 , 109, 103703	2.5	14
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468	Asymmetric split-vacancy defects in SiC polytypes: a combined theoretical and electron spin resonance study. <i>Physical Review Letters</i> , 2011 , 107, 195501	7.4	22
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465	A SiC Varactor With Large Effective Tuning Range for Microwave Power Applications. <i>IEEE Electron Device Letters</i> , 2011 , 32, 788-790	4.4	16
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458	Chloride Based CVD of 3C-SiC on (0001) SiC Substrates. <i>Materials Science Forum</i> , 2011 , 679-680, 75-78	0.4	6
457	Observation of Bistable Defects in Electron Irradiated N-Type 4H-SiC. <i>Materials Science Forum</i> , 2011 , 679-680, 249-252	0.4	3
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455	Growth and Properties of SiC On-Axis Homoepitaxial Layers. <i>Materials Science Forum</i> , 2010 , 645-648, 83-88	0.4	9
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425	Growth of Thick 4H-SiC Epitaxial Layers on On-Axis Si-Face Substrates with HCl Addition. <i>Materials Science Forum</i> , 2009 , 615-617, 93-96	0.4	7
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333	Observation of Vacancy Clusters in HTCVD Grown SiC. <i>Materials Science Forum</i> , 2005 , 483-485, 469-472	0.4	2
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331	Electron Paramagnetic Resonance of Shallow Phosphorous Centers in 4H- and 6H-SiC. <i>Materials Science Forum</i> , 2005 , 483-485, 515-518	0.4	5
330	Theoretical Investigations of Complexes of p-Type Dopants and Carbon Interstitial in SiC: Bistable, Negative-U Defects. <i>Materials Science Forum</i> , 2005 , 483-485, 519-522	0.4	5
329	Recombination Enhanced Defect Annealing in 4H-SiC. <i>Materials Science Forum</i> , 2005 , 483-485, 369-372	0.4	4
328	Effective-Mass Theory of Shallow Donors in 4H-SiC. <i>Materials Science Forum</i> , 2005 , 483-485, 511-514	0.4	5
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305	EPR and theoretical studies of positively charged carbon vacancy in 4H-SiC. <i>Physical Review B</i> , 2004 , 70,	3.3	43
304	Defects in High-Purity Semi-Insulating SiC. <i>Materials Science Forum</i> , 2004 , 457-460, 437-442	0.4	51
303	SiC Crystal Growth by HTCVD. <i>Materials Science Forum</i> , 2004 , 457-460, 9-14	0.4	51
302	Growth of Homoepitaxial Films on 4H-SiC(11-20) and 8 \times Off-Axis 4H-SiC(0001) Substrates and their Characterization. <i>Materials Science Forum</i> , 2004 , 457-460, 221-224	0.4	2

301	Characterization of GaN/SiC Epilayers by Picosecond Four-Wave Mixing Technique. <i>Physica Scripta</i> , 2004 , T114, 231-232	2.6	
300	Characteristics of Ni Schottky Contacts on Compensated 4H-SiC Layers. <i>Materials Science Forum</i> , 2003 , 433-436, 709-712	0.4	1
299	Defects in SiC. <i>Physica B: Condensed Matter</i> , 2003 , 340-342, 15-24	2.8	17
298	Anti-site pair in SiC: a model of the DI center. <i>Physica B: Condensed Matter</i> , 2003 , 340-342, 175-179	2.8	7
297	Boron-related luminescence in SiC. <i>Physica B: Condensed Matter</i> , 2003 , 340-342, 141-145	2.8	3
296	Predicted nitrogen doping concentrations in silicon carbide epitaxial layers grown by hot-wall chemical vapor deposition. <i>Journal of Crystal Growth</i> , 2003 , 250, 471-478	1.6	25
295	Reducing stress in silicon carbide epitaxial layers. <i>Journal of Crystal Growth</i> , 2003 , 252, 289-296	1.6	8
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292	Using N ₂ as precursor gas in III-nitride CVD growth. <i>Journal of Crystal Growth</i> , 2003 , 253, 26-37	1.6	19
291	Aluminum doping of epitaxial silicon carbide. <i>Journal of Crystal Growth</i> , 2003 , 253, 340-350	1.6	51
290	Structural impact of LPE buffer layer on sublimation grown 4H-SiC epilayers. <i>Journal of Crystal Growth</i> , 2003 , 256, 276-282	1.6	3
289	Comparison of SiC sublimation epitaxial growth in graphite and TaC coated crucibles. <i>Diamond and Related Materials</i> , 2003 , 12, 1936-1939	3.5	7
288	Photoluminescence Up-Conversion Processes in SiC. <i>Materials Science Forum</i> , 2003 , 433-436, 309-312	0.4	
287	HTCVD Grown Semi-Insulating SiC Substrates. <i>Materials Science Forum</i> , 2003 , 433-436, 33-38	0.4	47
286	Correlation between the antisite pair and the DI center in SiC. <i>Physical Review B</i> , 2003 , 67,	3.3	66
285	Hydrogen passivation of nitrogen in SiC. <i>Applied Physics Letters</i> , 2003 , 83, 1385-1387	3.4	15
284	Defects in Semi-Insulating SiC Substrates. <i>Materials Science Forum</i> , 2003 , 433-436, 45-50	0.4	28

283	Correlation between Electrical and Optical Mapping of Boron Related Complexes in 4H-SiC. <i>Materials Science Forum</i> , 2003 , 433-436, 423-426	0.4	2
282	Growth of High Quality p-Type 4H-SiC Substrates by HTCVD. <i>Materials Science Forum</i> , 2003 , 433-436, 21-24	0.4	6
281	Orientation-Dependent Defect Formation in Silicon Carbide Epitaxial Layers. <i>Materials Science Forum</i> , 2003 , 433-436, 281-284	0.4	2
280	Origin and Behaviour of Deep Levels in Sublimation Growth of 4H-SiC Layers. <i>Materials Science Forum</i> , 2003 , 433-436, 169-172	0.4	
279	Predictions of Nitrogen Doping in SiC Epitaxial Layers. <i>Materials Science Forum</i> , 2003 , 433-436, 137-140	0.4	
278	Effect of Ambient on 4H-SiC Bulk Crystals Grown by Sublimation. <i>Materials Science Forum</i> , 2003 , 433-436, 75-78	0.4	1
277	Implementation of Hot-Wall MOCVD to the Growth of High-Quality GaN on SiC. <i>Materials Science Forum</i> , 2003 , 433-436, 991-994	0.4	2
276	Calculation of Hyperfine Constants of Defects in 4H-SiC. <i>Materials Science Forum</i> , 2003 , 433-436, 511-514	0.4	14
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274	The Effect of Thermal Gradients on SiC Wafers. <i>Materials Science Forum</i> , 2003 , 433-436, 193-196	0.4	3
273	Nitrogen Delta Doping in 4H-SiC Epilayers. <i>Materials Science Forum</i> , 2003 , 433-436, 153-156	0.4	4
272	A Comparison of MESFETs on Different 4H-Silicon Carbide Semi-Insulating Substrates. <i>Materials Science Forum</i> , 2003 , 433-436, 737-740	0.4	3
271	Simulation and Measurement of Switching Characteristics of 4H-SiC Buried-Gate JFETs. <i>Materials Science Forum</i> , 2003 , 433-436, 773-776	0.4	
270	Time-Resolved Photoluminescence of Deep Centers in Semi-Insulating 4H-SiC. <i>Materials Science Forum</i> , 2003 , 433-436, 301-304	0.4	2
269	Donor-Acceptor Pair Luminescence in 4H-SiC Doped with Nitrogen and Aluminum. <i>Materials Science Forum</i> , 2003 , 433-436, 321-324	0.4	1
268	Properties of Different Stacking Faults that Cause Degradation in SiC PiN Diodes. <i>Materials Science Forum</i> , 2003 , 433-436, 913-916	0.4	3
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232	Growth Characteristics of SiC in a Hot-Wall CVD Reactor with Rotation. <i>Materials Science Forum</i> , 2002 , 389-393, 191-194	0.4	3
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229	Impurity-Controlled Dopant Activation - The Role of Hydrogen in p-Type Doping of SiC. <i>Materials Science Forum</i> , 2002 , 389-393, 561-564	0.4	3
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227	Lateral Enlargement of Silicon Carbide Crystals. <i>Materials Science Forum</i> , 2002 , 389-393, 39-42	0.4	5
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225	The Neutral Silicon Vacancy in SiC: Ligand Hyperfine Interaction. <i>Materials Science Forum</i> , 2002 , 389-393, 501-504	0.4	8
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221	Influence of Epitaxial Layer on SiC Schottky Diode Gas Sensors Operated under High-Temperature Conditions. <i>Materials Science Forum</i> , 2002 , 389-393, 1423-1426	0.4	2
220	Effect of Temperature Treatment on Au/Pd Schottky Contacts to 4H-SiC. <i>Materials Science Forum</i> , 2002 , 389-393, 929-932	0.4	1
219	Growth of AlN Films by Hot-Wall CVD and Sublimation Techniques: Effect of Growth Cell Pressure. <i>Materials Science Forum</i> , 2002 , 389-393, 1469-1472	0.4	1
218	Incorporation of Hydrogen (1H and 2H) into 4H-SiC during Epitaxial Growth. <i>Materials Science Forum</i> , 2002 , 389-393, 565-568	0.4	6
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116	Cathodoluminescence of Defect Regions in SiC Epi-Films. <i>Materials Science Forum</i> , 1998 , 264-268, 653-656	0.4	6
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105	Observation of Metastable Defect in Electron Irradiated 6H-SiC. <i>Materials Science Forum</i> , 1998 , 264-268, 561-564	0.4	5
104	The Neutral Silicon Vacancy in 6H and 4H SiC. <i>Materials Science Forum</i> , 1998 , 264-268, 473-476	0.4	8

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